POLISHER

The 6EZ makes SiC polish EZ!

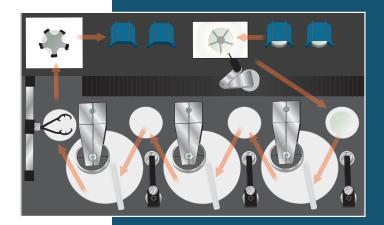


KEY FEATURES:

- Fully-automated, cassette-to- cassette handling
- Single wafer processing for excellent wafer-to-wafer control
- Single-side and two-sided polish
- Three tables with dedicated carriers, pad conditioners, and pad cleaners
- Acid-resistant components
- OCR (optional)
- State-of-the-art control architecture and Windowsbased operating system
- Two standard slurry delivery lines, optional third slurry line available
- Factory host communication (optional)
- SEMI S2, S8, and CE certified
- 50-wafer processing without operator intervention
- Integrated post-polish clean

It's no secret that SiC is a hard material to process. We understand the challenges of working with SiC and we have applied our knowledge of SiC grinding, prime wafer polishing, and CMP technology to develop a unique solution that truly makes polishing SiC easy.

We are pleased to introduce you to the **6EZ**, the world's first fully-automated, single wafer, dry-in-dry-out polisher designed specifically for SiC.



POLISH MODULE WITH DEDICATED HARDWARE

The 6EZ polish section consists of three polish tables, three spindles, and an integrated post-polish cleaning module. Each table comes standard with a dedicated spindle, carrier, pad conditioner and high-pressure spray bar (pad cleaner), which provides the best possible wafer-to-wafer process control. In addition, all tables can be configured with up to three slurries (optional).

INTEGRATED CLEANING

Extra attention has been given to keep the wafers and the polisher clean by integrating wet transfer stations, sprays, rinses and a separate post-polish wafer cleaning module.

Wafers are kept wet in between polish steps. Every wafer is run through a post-polish cleaning for the removal of slurry particles after the final polish and returned to the same cassette and slot at the completion of the polish sequence. The wafers are then ready for a pre-Epi clean.



CLEANROOM READY

HEPA filtration and a cleanroom compatible EFEM offer the option to install the 6EZ either bulkhead or ballroom style.

LOW pH COMPATIBLE

Materials used on the 6EZ are selected to be compatible with acidic SiC slurries.

TTV CONTROL

Plate-style carriers with adjustable back pressure provide superior TTV control without the need for wafer sorting prior to polish.

FULLY-AUTOMATED

Up to 50 wafers can be loaded into the machine and will be automatically polished on either a single side or both sides depending on the recipe selected. In a two-sided polish process, the machine polishes the carbon face first and automatically flips, cleans, and then polishes the silicon face of the wafers without operator intervention.

PRODUCTION PROVEN TECHNOLOGY

Built for high reliability, the 6EZ uses production- proven wafer carrier, spindle overarm, pad conditioning, and table rotation technology.

USER FRIENDLY

The user-friendly GUI and intuitive operator menus make recipe selection quick and simple. Maintenance and pad changes are easy to complete via multiple ergonomic access points around the machine.





SINGLE WAFER PROCESSING RESULTS IN HIGHER YIELD

Single wafer processing means that each wafer is processed individually, rather than in a batch. Each wafer sees the same process conditions, which results in much better process control and wafer-to-wafer consistency.

Higher wafer yield, however, is the key advantage of single wafer processing.



TYPICAL SIC BATCH PROCESS FLOW



60% FEWER MACHINE-TO-MACHINE HANDOFFS COMPARED TO BATCH



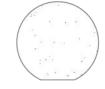
By combining Revasum's 7AF-HMG grinder and the 6EZ polisher, the entire process flow from wire slicing or laser splitting to EPI is synchronized to provide optimum performance and high yields at an affordable cost per wafer. Delivering a production-ready solution for 150mm and 200mm SiC substrate manufacturing.

SURFACE FINISH SIC SI-FACE



THE 6EZ PRODUCES A

DAMAGE-FREE SURFACE



Batch Polish 19,999 scratches

6EZ Single Wafer0 scratches



Surface Roughness measured by AFM over 5 μ m x 5 μ m area, at mid-radius (~35mm) from the wafer center.

ADVANTAGES OF SINGLE WAFER POLISHING

Revasum specializes in single wafer processing equipment, because single wafer processing:

- Provides better control over TTV and surface quality
- Eliminates the need for wafer sorting
- Reduces the number of machine-to-machine wafer transfer steps
- Lowers wafer breakage risk
- Improves cleanliness
- Enables process automation
- Increases productivity
- Achieves higher wafer yields



revasum.com/6EZ

7AF-HMG Wafer Grinder

Designed for Advanced Grinding of Hard Materials

SYSTEM OVERVIEW

Revasum's 7AF-HMG grinding solution extends wheel life by nine times, increases uptime by 10%, boosts wafer output by 15 percent, and reduces the cost of ownership by seven times. With a return on investment of less than one year, the choice for SiC grinding is clear: choose the 7AF-HMG.

WHEEL LIFE IS NINE TIMES BETTER*

A SELF-DRESSING GRIND PROCESS*

THE RETURN ON INVESTMENT IS LESS THAN 12 MONTHS*

88 PERCENT FEWER WHEEL CHANGES*



*When back grinding SiC Wafers with 550µm target removal, and annual production of 25,000 wafers

FEATURES

Real-time grind performance monitoring

A self-dressing grind process

Grind spindles can be fitted with coarse or fine wheels

Supports dual fine grind, dual coarse grind, and standard coarse/fine grind processing

Wafer flipping available for double-side grinding applications

In-situ, real-time thickness control

Air bearing spindles equipped with 8Hp motors

Robust, contemporary Windows 7 based operating system

BENEFITS

Achieves <1µm TTV for most applications

Astounding performance on wire sawn SiC wafers

Designed to reduce consumables and operations costs

Accommodates incoming wafers with varied thicknesses without presorting

A wide process window, reduces setup time and increases process repeatability

Surface finish can be optimized for subsequent processing

Easy to maintain and to switch between wafer sizes

Flexible process flows



7AF-HMG Wafer Grinder

Designed for Advanced Grinding of Hard Materials



GRINDING ACCURACY

TTV Within Wafer -< 1µm Thickness Variation -<u>+</u> 1µm

Surface Roughness -200 Å to 30 Å (wheel dependent) Based on Si grinding

GRINDING

Grind Spindle Type -Air Bearing Grind Spindle Speed -500-4300 RPM

Grind Spindle Motor Output -8Hp

Work Chuck Speed -20-700 RPM

Work Chuck Type -Ceramic, porous vacuum

Spin / Rinse / Dry -Vacuum Chuck



TECHNICAL SPECS

(SAE) 73"W x 85" D x 76" H Dimensions -(Metric) 1.86M x 2.15M x 2.46M

~42.6 Ft² [3.98 M²] Footprint -~8500 lbs [~3865 K] Weight -50mm to 200mm Wafer Capacity -In-situ, contact probe Wafer Measurement -Wafer Handling -Fully Automated Load/Unload -1 send, 1 receive Configuration -2 chucks, 2 spindles

PPLICATION

7AF-HMG is used for backside thinning and for bulk thinning of wire-sawn substrates for a hard materials, including:

- SiC
- InP
- Ge
- GaAs
- GaN
 - and
- Sapphire LiNbO3
- more...

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